

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_C = +25^\circ\text{C}$
-20V	5.5mΩ @ $V_{GS} = -10\text{V}$	-40A
	7.0mΩ @ $V_{GS} = -4.5\text{V}$	-40A
	9.0mΩ @ $V_{GS} = -2.5\text{V}$	-40A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high- efficiency power management applications.

Applications

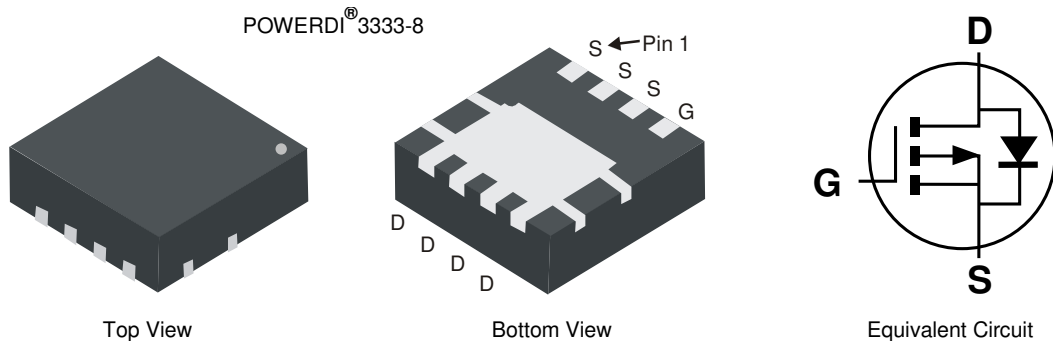
- Load Switch
- Power Management Functions

Features

- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: POWERDI® 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (B3)
- Weight: 0.030 grams (Approximate)

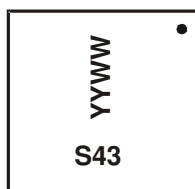


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2007UFG-7	POWERDI3333-8	2,000/Tape & Reel
DMP2007UFG-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



S43 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 14 = 2014)
WW = Week Code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C T _C = +25°C	I _D	-18.0 -14.5 -40	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-2.2	A
Avalanche Current L=0.1mH			I _{AS}	-30	A
Avalanche Energy L=0.1mH			E _{AS}	50	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	2.3	W
	T _C = +25°C		41	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	58	°C/W
	(Note 6)		143	
Thermal Resistance, Junction to Case		R _{θJC}	3.0	°C
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.3	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	4.4	5.5	mΩ	V _{GS} = -10V, I _D = -15A
		—	4.9	7.0		V _{GS} = -4.5V, I _D = -15A
		—	6.5	9.0		V _{GS} = -2.5V, I _D = -10A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -10A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	4,621	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	652	—		
Reverse Transfer Capacitance	C _{rss}	—	403	—		
Gate Resistance	R _G	—	3.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	39	—	nC	V _{DD} = -10V, I _D = -20A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	85	—		
Gate-Source Charge	Q _{gs}	—	8.3	—		
Gate-Drain Charge	Q _{gd}	—	9.6	—		
Turn-On Delay Time	t _{D(ON)}	—	10.1	—	ns	V _{GS} = -4.5V, V _{DD} = -10V, R _G = 1Ω, I _D = -10A
Turn-On Rise Time	t _R	—	9.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	61	—		
Turn-Off Fall Time	t _F	—	51	—		
Reverse Recovery Time	t _{RR}	—	20.1	—	ns	I _F = -10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{rr}	—	10.1	—	nC	I _F = -10A, di/dt = 100A/µs

- Notes:
1. R_{θJA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{θJC} is guaranteed by design while R_{θJA} is determined by the user's board design.
 2. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 3. Short duration pulse test used to minimize self-heating effect.
 4. Guaranteed by design. Not subject to product testing.

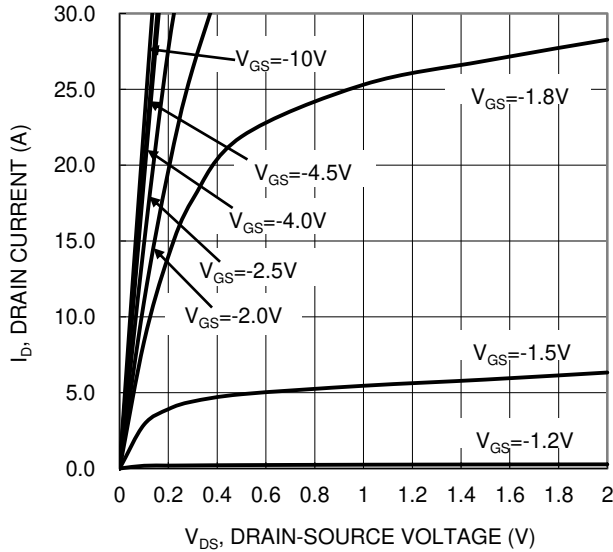


Figure 1. Typical Output Characteristic

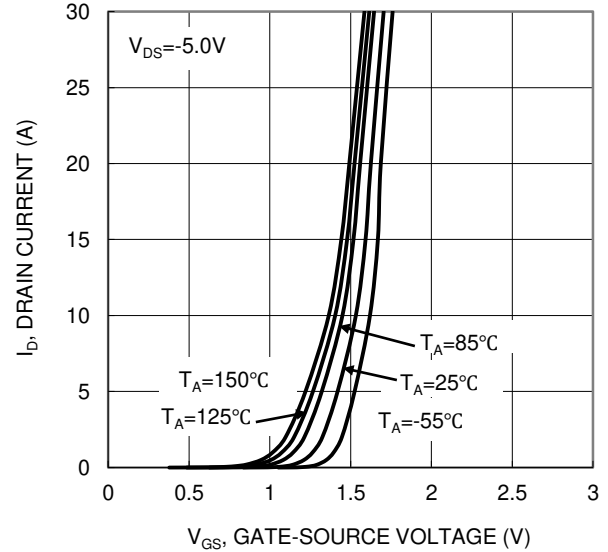


Figure 2. Typical Transfer Characteristic

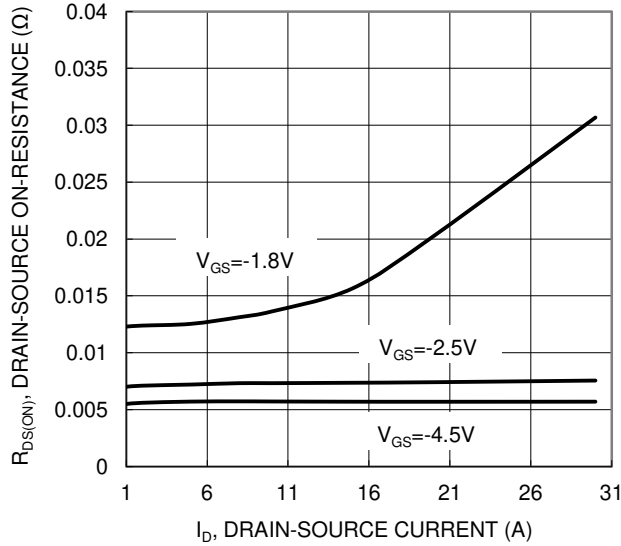


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

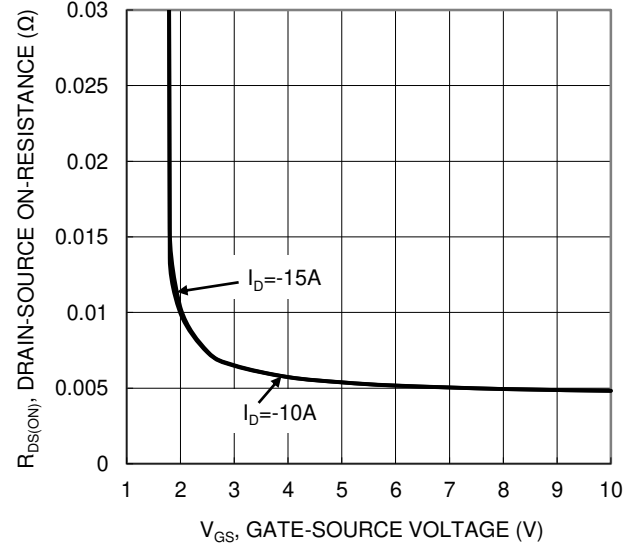


Figure 4. Typical Transfer Characteristic

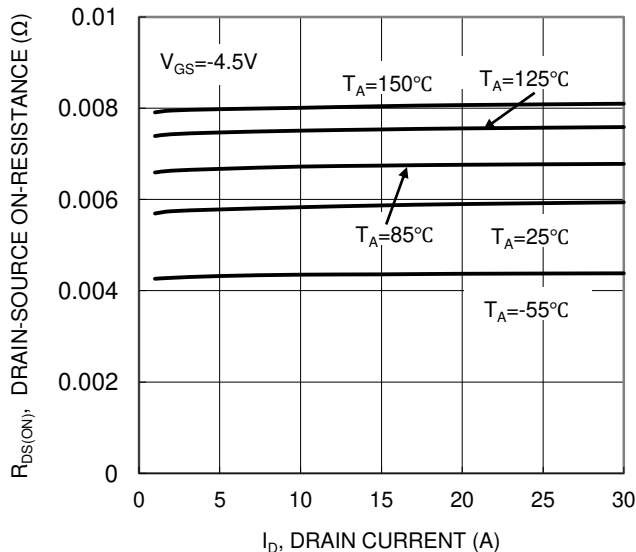


Figure 5. Typical On-Resistance vs Drain Current and Temperature

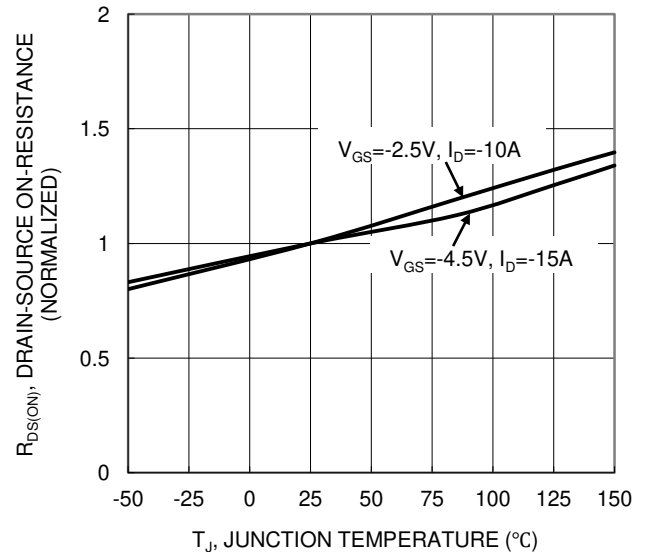
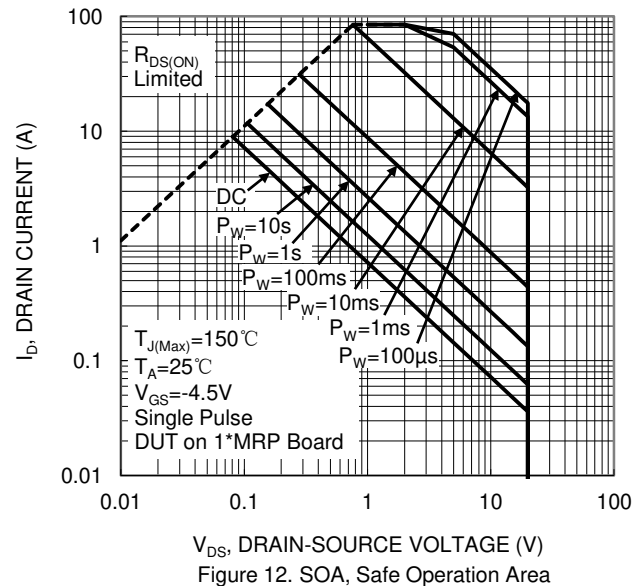
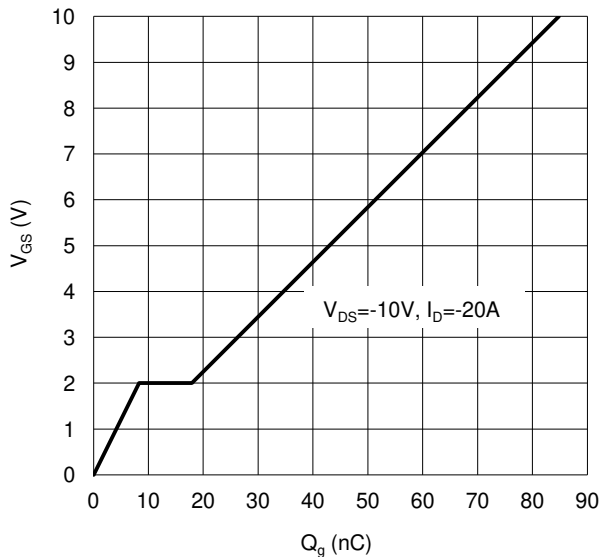
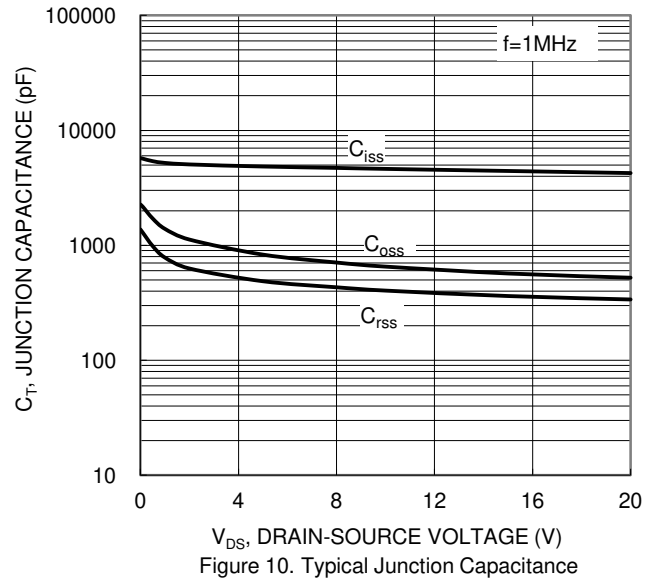
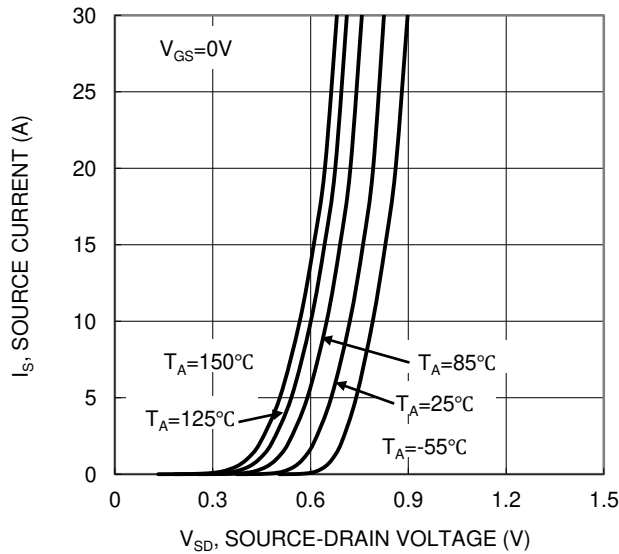
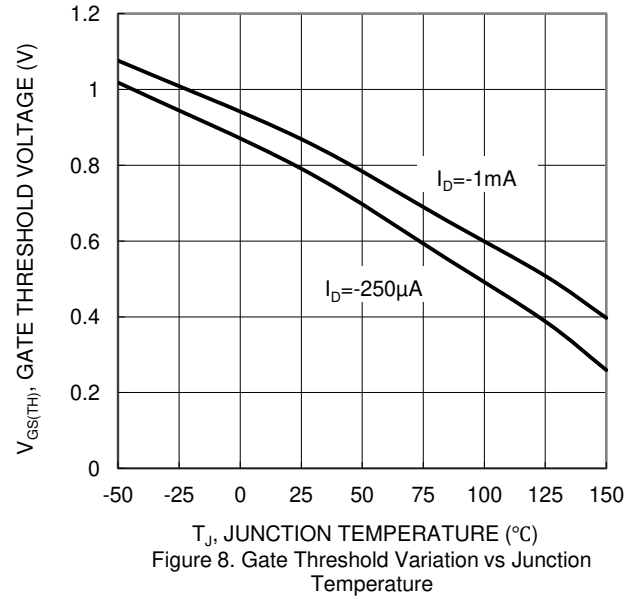
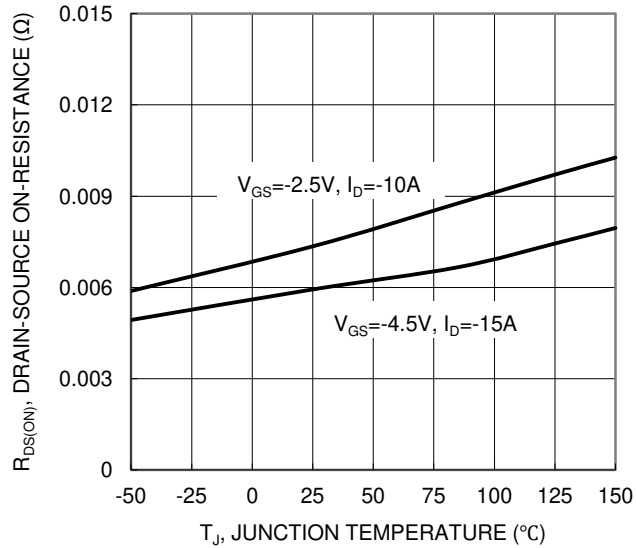


Figure 6. On-Resistance Variation with Temperature



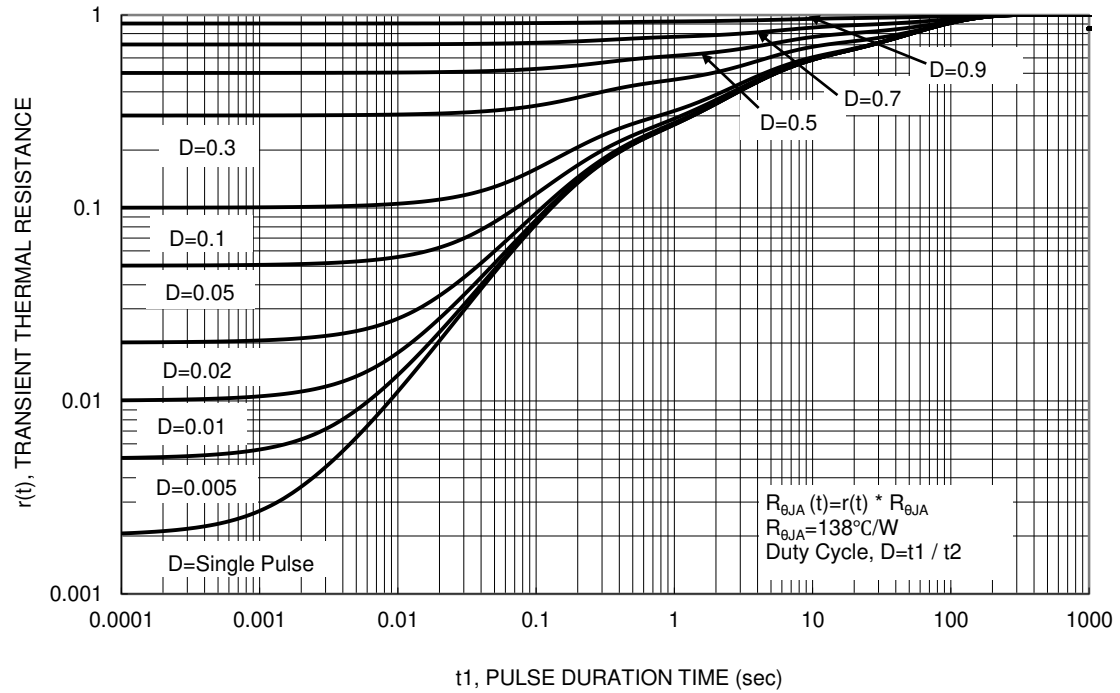
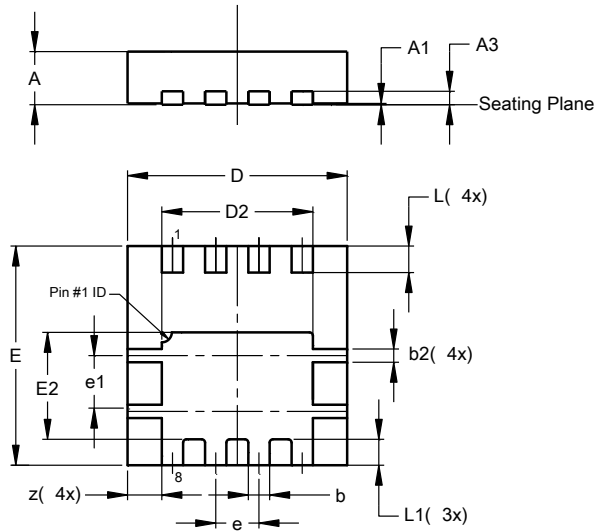


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

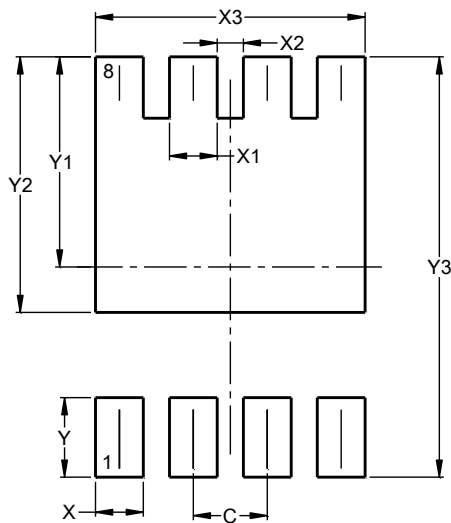
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI [®] 3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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